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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	221
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	324-BGA
Supplier Device Package	324-FBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe3000-2fg324

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLXL exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-1 on page 2-4 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3E FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

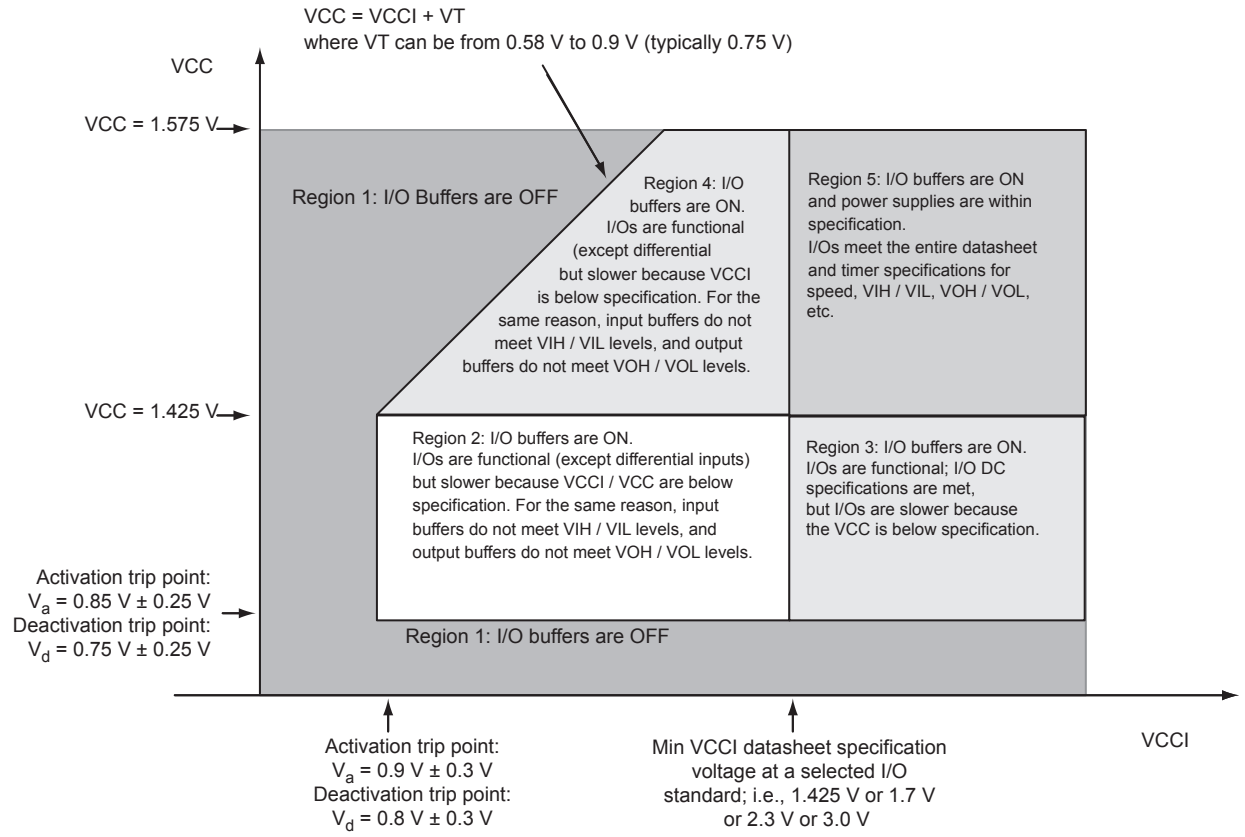


Figure 2-1 • **I/O State as a Function of VCCI and VCC Voltage Levels**

User I/O Characteristics

Timing Model

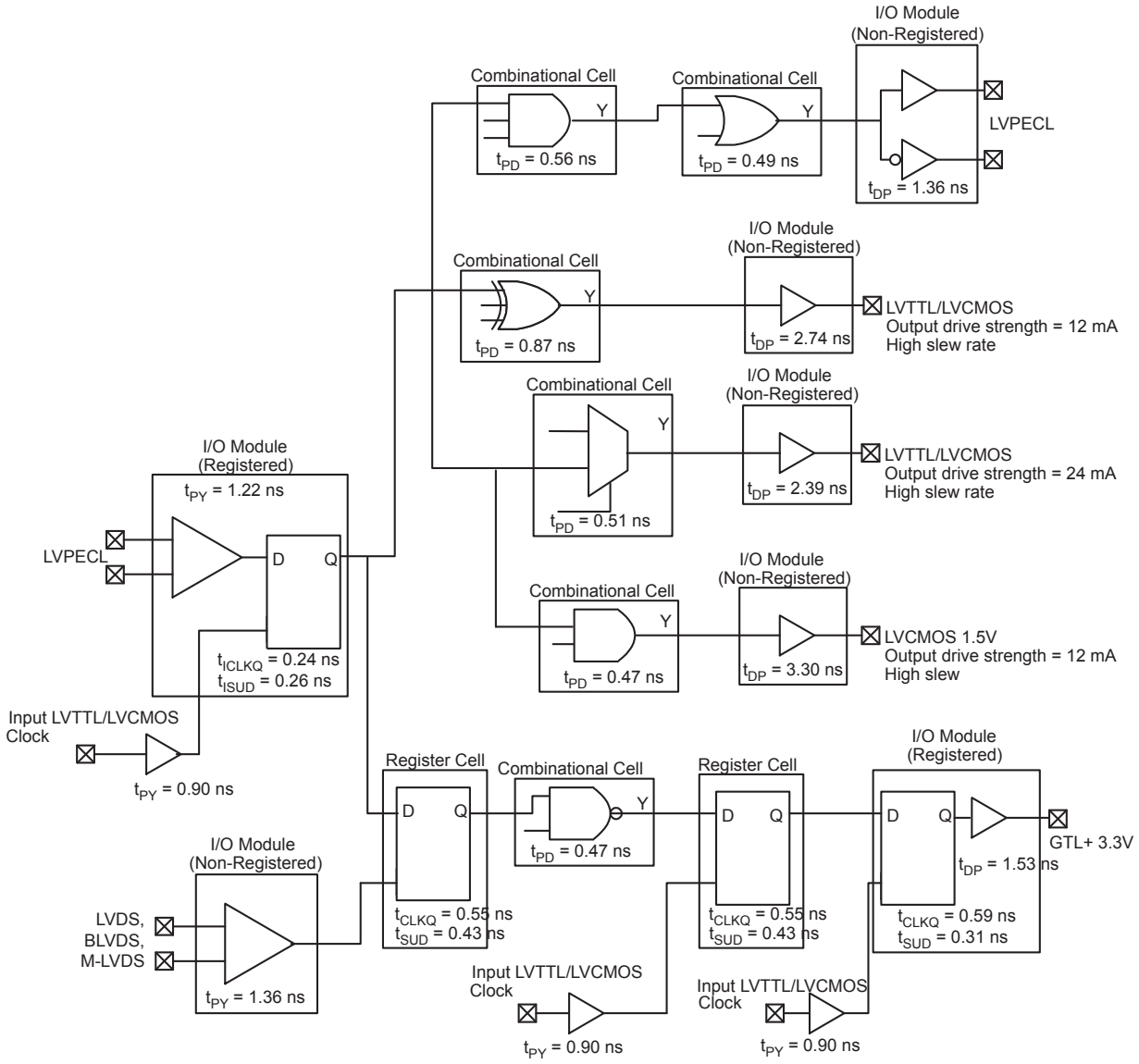


Figure 2-2 • **Timing Model**
Operating Conditions: –2 Speed, Commercial Temperature Range (T_J = 70°C), Worst-Case VCC = 1.425 V

***Table 2-22* • Duration of Short Circuit Event Before Failure (continued)**

Temperature	Time before Failure
85°C	2 years
100°C	6 months

***Table 2-23* • Schmitt Trigger Input Hysteresis**
Hysteresis Voltage Value (typ.) for Schmitt Mode Input Buffers

Input Buffer Configuration	Hysteresis Value (typ.)
3.3 V LVTTL/LVCMOS/PCI/PCI-X (Schmitt trigger mode)	240 mV
2.5 V LVCMOS (Schmitt trigger mode)	140 mV
1.8 V LVCMOS (Schmitt trigger mode)	80 mV
1.5 V LVCMOS (Schmitt trigger mode)	60 mV

Table 2-24* • I/O Input Rise Time, Fall Time, and Related I/O Reliability

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS (Schmitt trigger disabled)	No requirement	10 ns *	20 years (110°C)
LVTTL/LVCMOS (Schmitt trigger enabled)	No requirement	No requirement, but input noise voltage cannot exceed Schmitt hysteresis.	20 years (110°C)
HSTL/SSTL/GTL	No requirement	10 ns *	10 years (100°C)
LVDS/B-LVDS/M-LVDS/ LVPECL	No requirement	10 ns *	10 years (100°C)

*Note: *For clock signals and similar edge-generating signals, refer to the "ProASIC3/E SSO and Pin Placement Guidelines" chapter of the ProASIC3E FPGA Fabric User's Guide. The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.*

3.3 V LVCMOS Wide Range

Table 2-29 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	109	103	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	127	132	10	10
100 µA	24 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	181	268	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

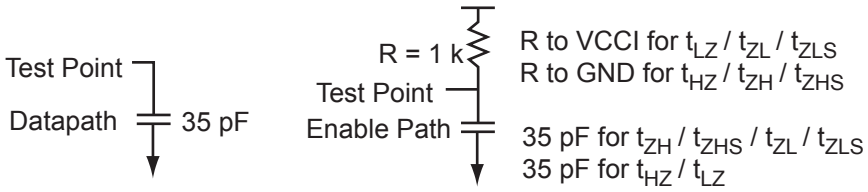


Figure 2-7 • AC Loading

Table 2-30 • 3.3 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	1.4	–	35

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

SSTL3 Class II

Stub-Speed Terminated Logic for 3.3 V memory bus standard (JESD8-8). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-75 • Minimum and Maximum DC Input and Output Levels

SSTL3 Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
21 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.5	VCCI – 0.9	21	21	109	103	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

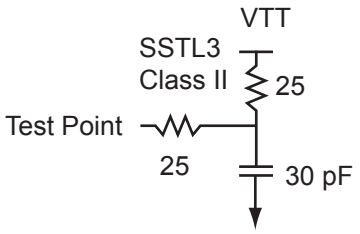


Figure 2-21 • AC Loading

Table 2-76 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.5	1.5	1.485	30

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-77 • SSTL3 Class II
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V, VREF = 1.5 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	2.07	0.04	1.25	0.43	2.10	1.67			4.34	3.91	ns
–1	0.56	1.76	0.04	1.06	0.36	1.79	1.42			3.69	3.32	ns
–2	0.49	1.54	0.03	0.93	0.32	1.57	1.25			3.24	2.92	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

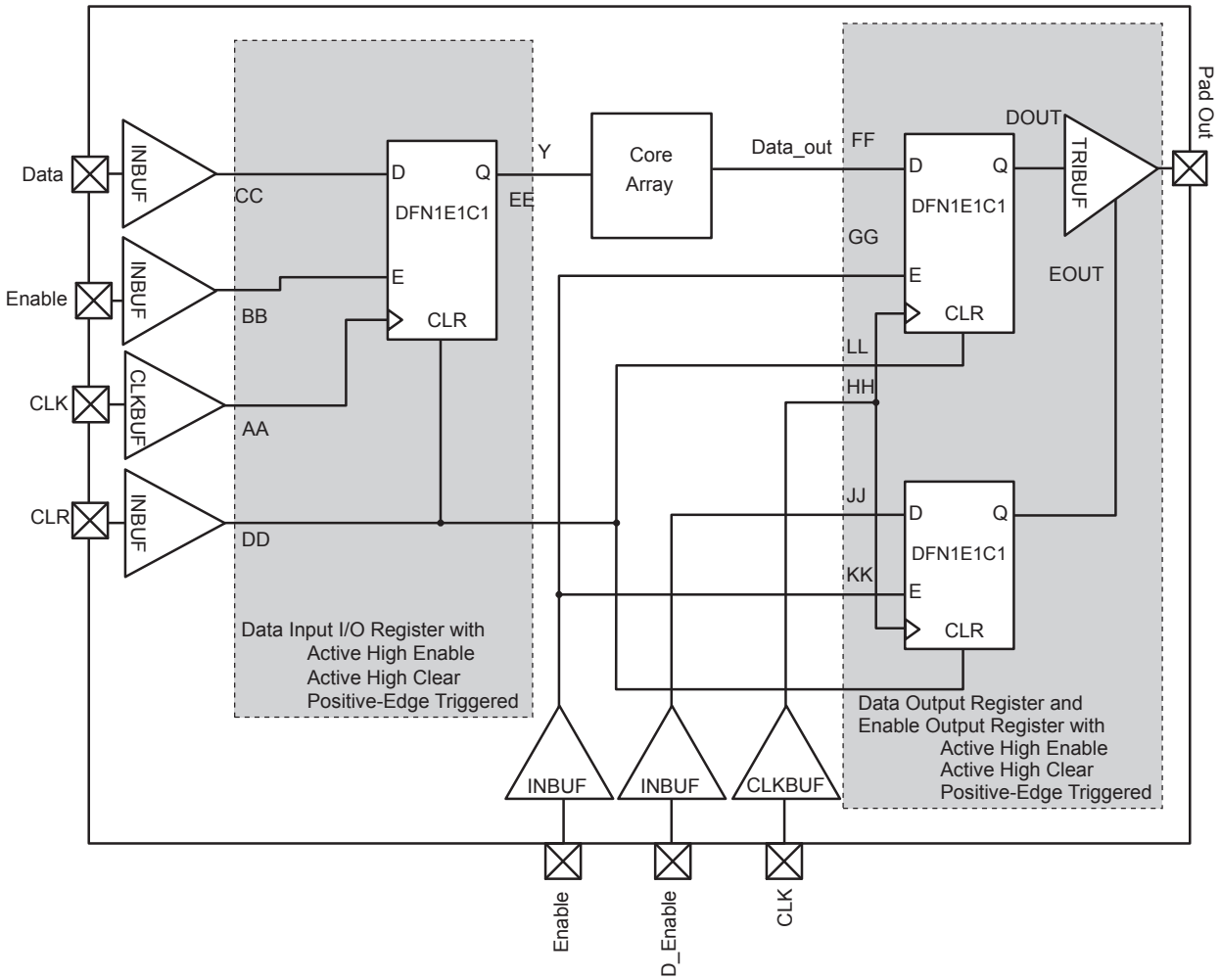


Figure 2-26 • **Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear**

DDR Module Specifications

Input DDR Module

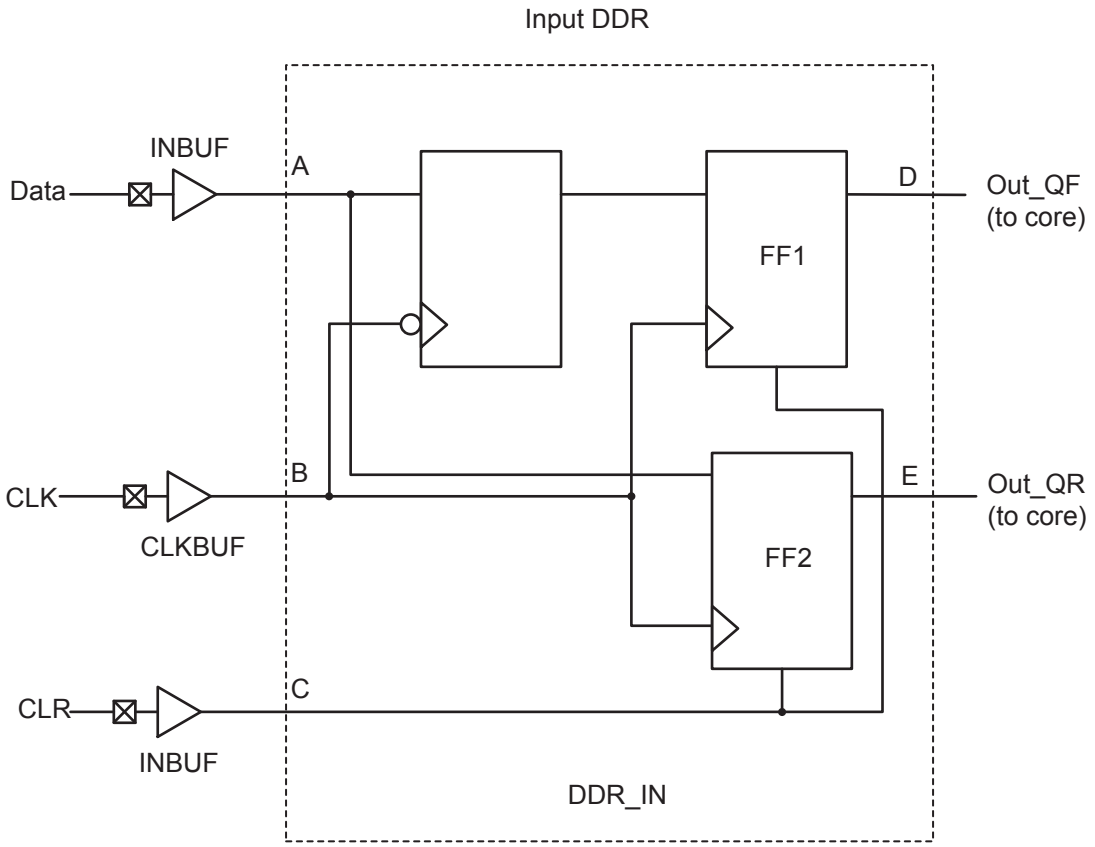


Figure 2-30 • **Input DDR Timing Model**

Table 2-89 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR	B, D
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF	B, E
$t_{DDRISUD}$	Data Setup Time of DDR input	A, B
t_{DDRIHD}	Data Hold Time of DDR input	A, B
$t_{DDRICLR2Q1}$	Clear-to-Out Out_QR	C, D
$t_{DDRICLR2Q2}$	Clear-to-Out Out_QF	C, E
$t_{DDRIREMCLR}$	Clear Removal	C, B
$t_{DDRIRECCLR}$	Clear Recovery	C, B

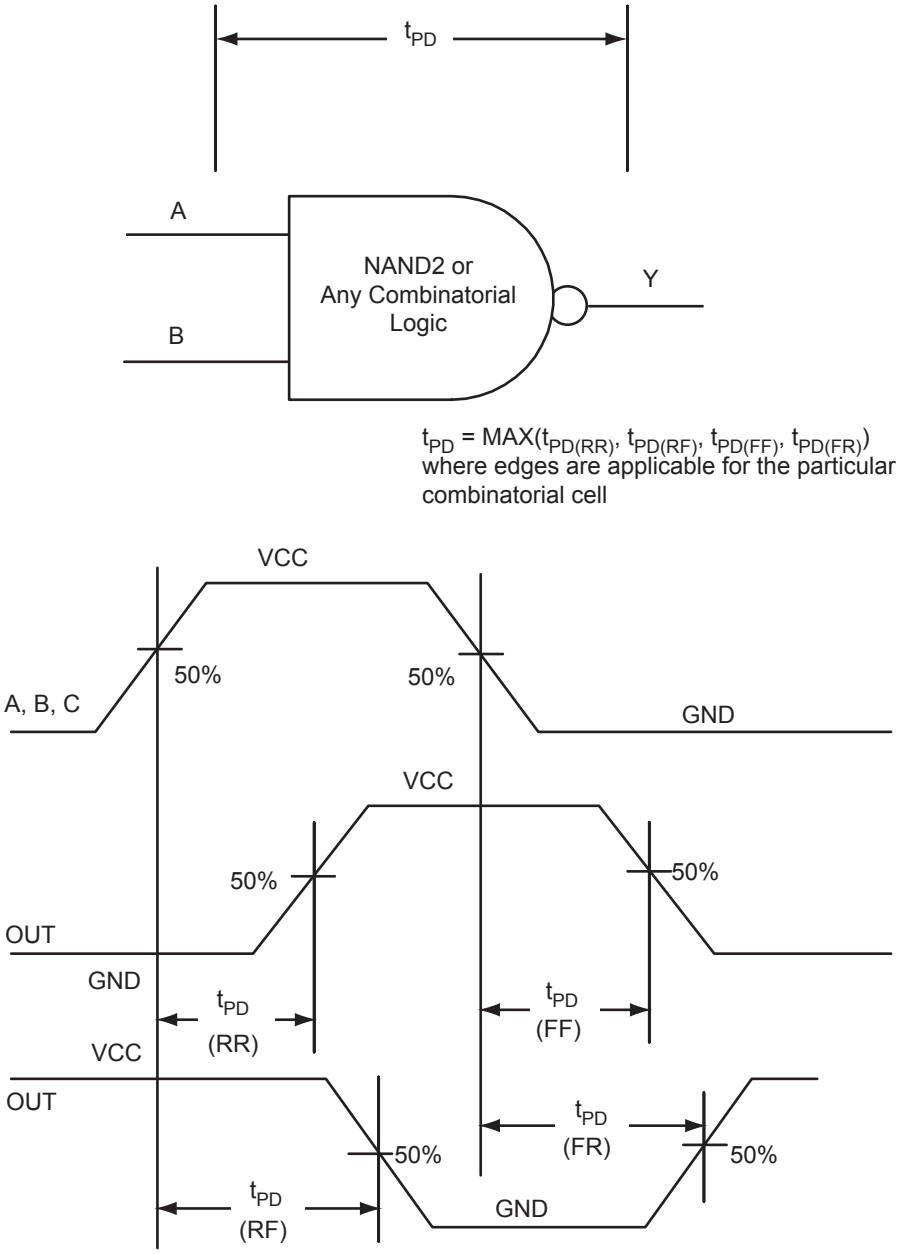


Figure 2-35 • **Timing Model and Waveforms**

Timing Waveforms

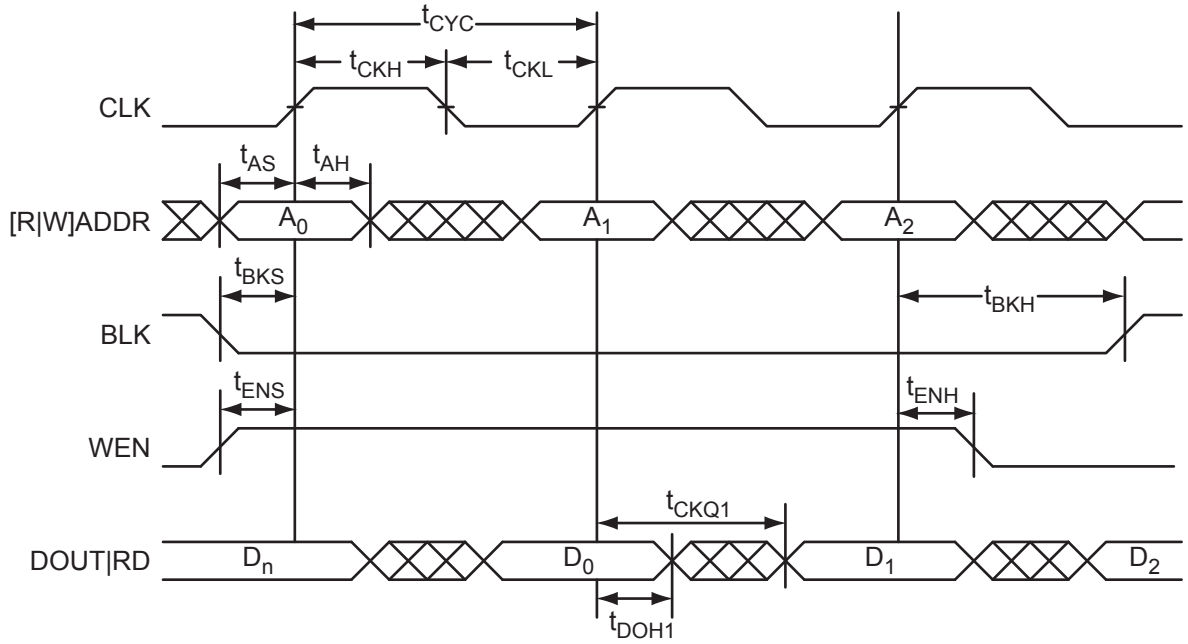


Figure 2-41 • **RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.**

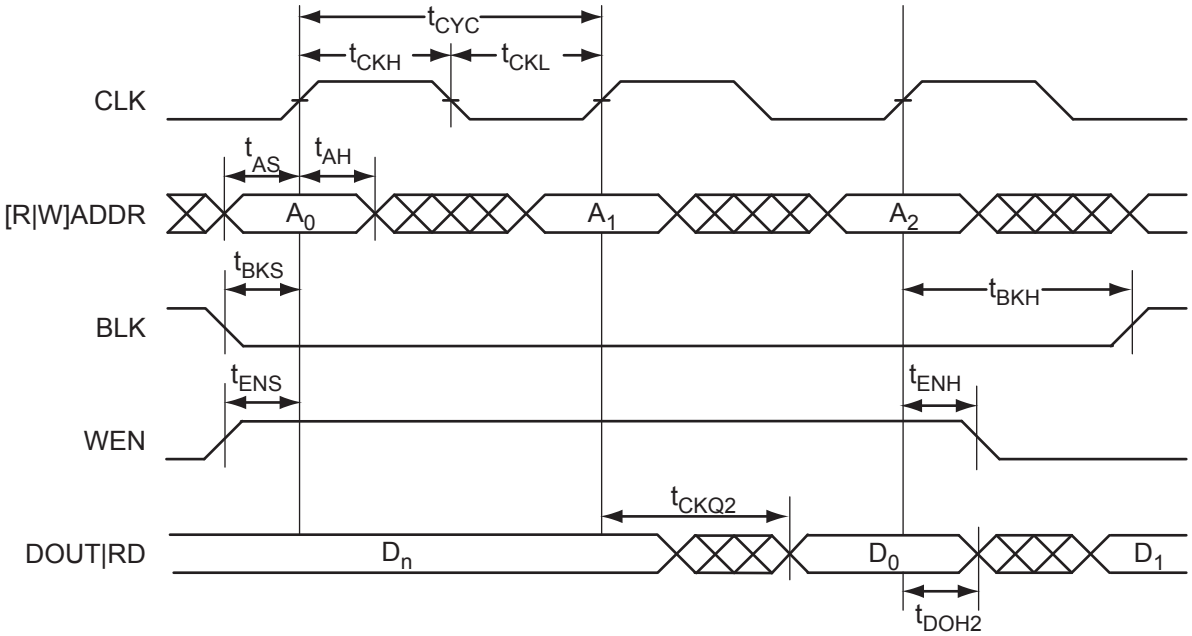


Figure 2-42 • **RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.**

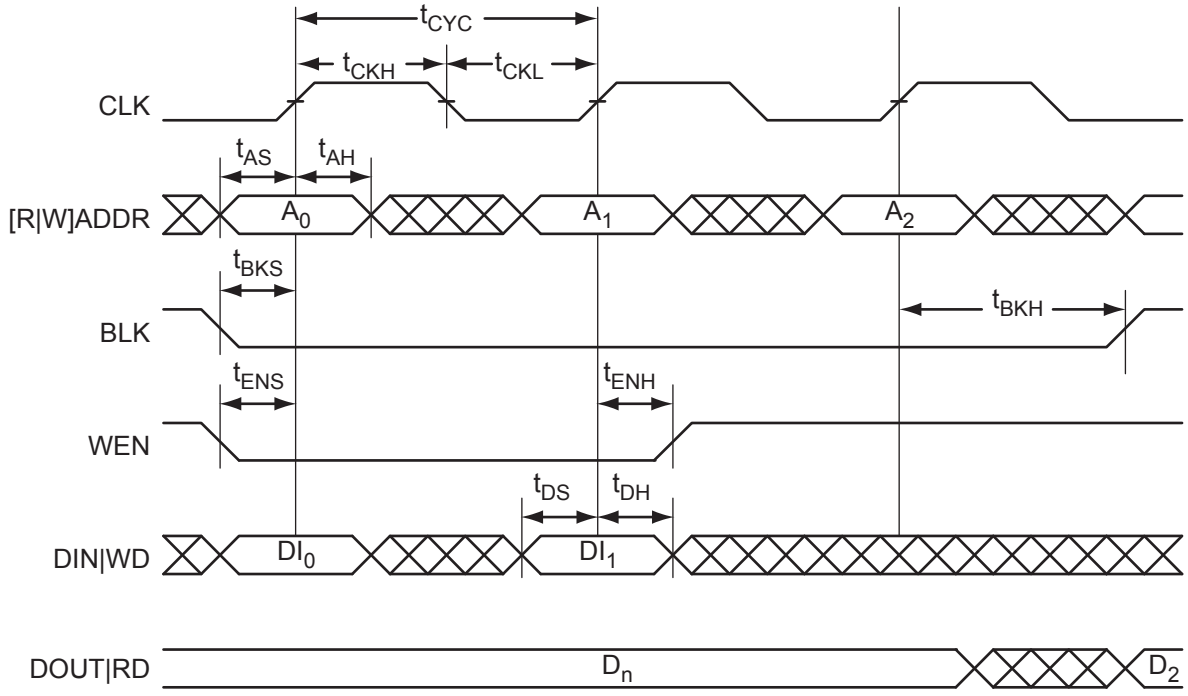


Figure 2-43 • **RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**

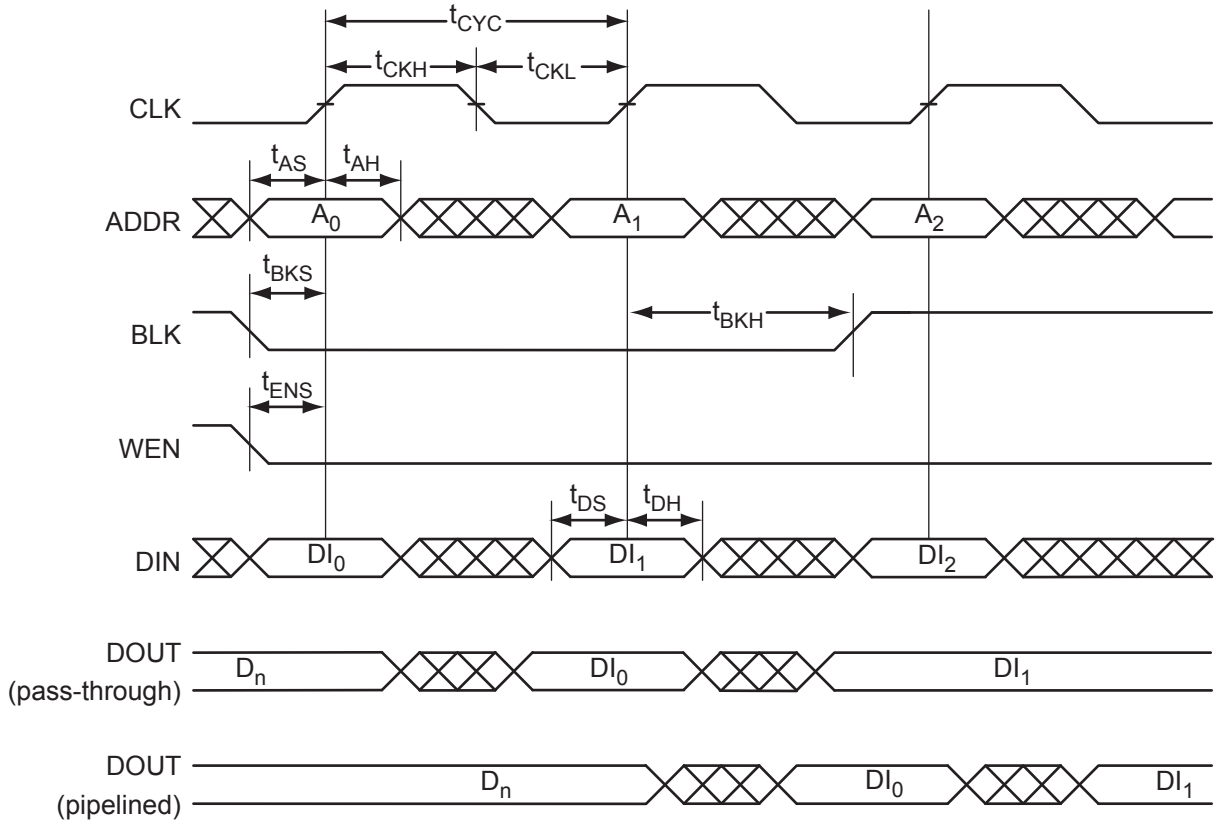


Figure 2-44 • **RAM Write, Output as Write Data. Applicable to RAM4K9 Only.**

Timing Characteristics

Table 2-99 • RAM4K9
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BLK hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.79	2.03	2.39	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWL} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t_{C2CWWH} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DO (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

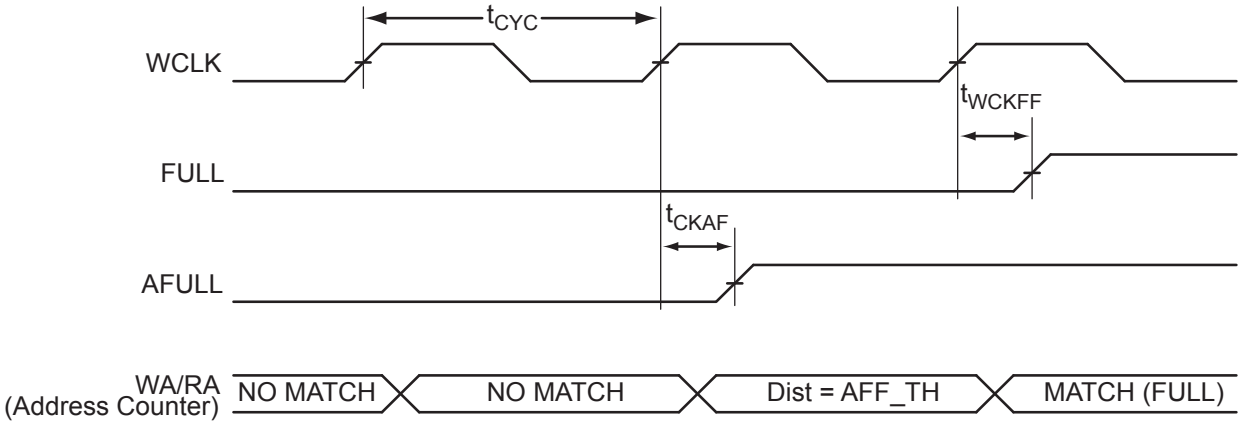


Figure 2-51 • **FIFO FULL Flag and AFULL Flag Assertion**

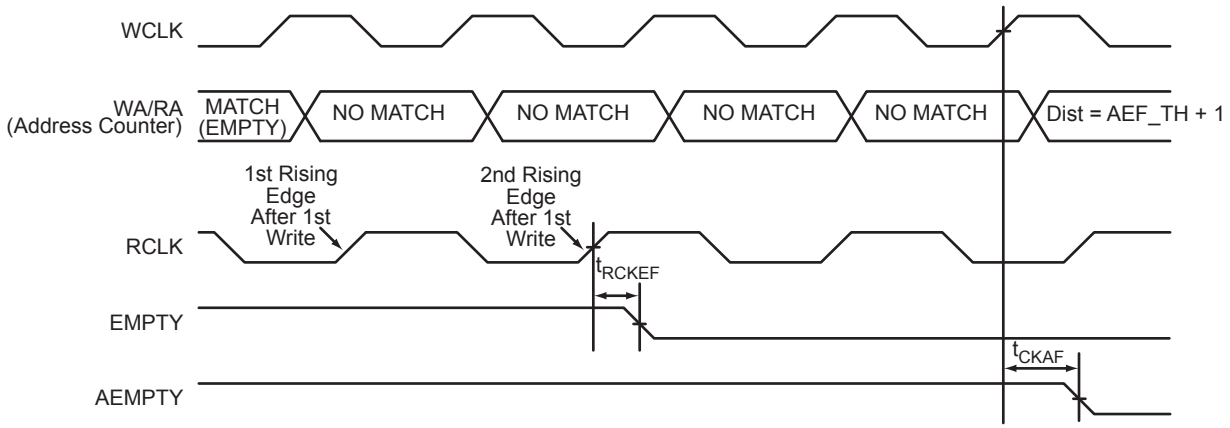


Figure 2-52 • **FIFO EMPTY Flag and AEMPTY Flag Deassertion**

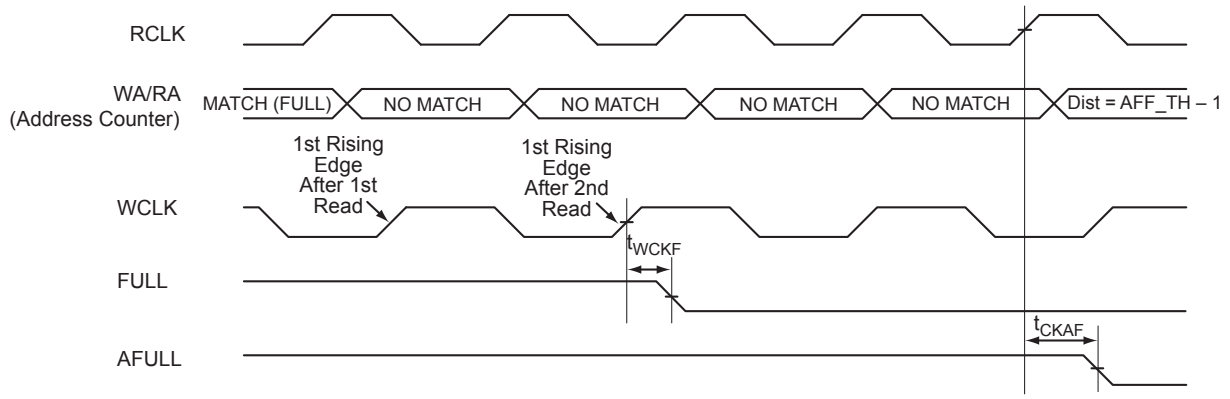


Figure 2-53 • **FIFO FULL Flag and AFULL Flag Deassertion**

Timing Characteristics

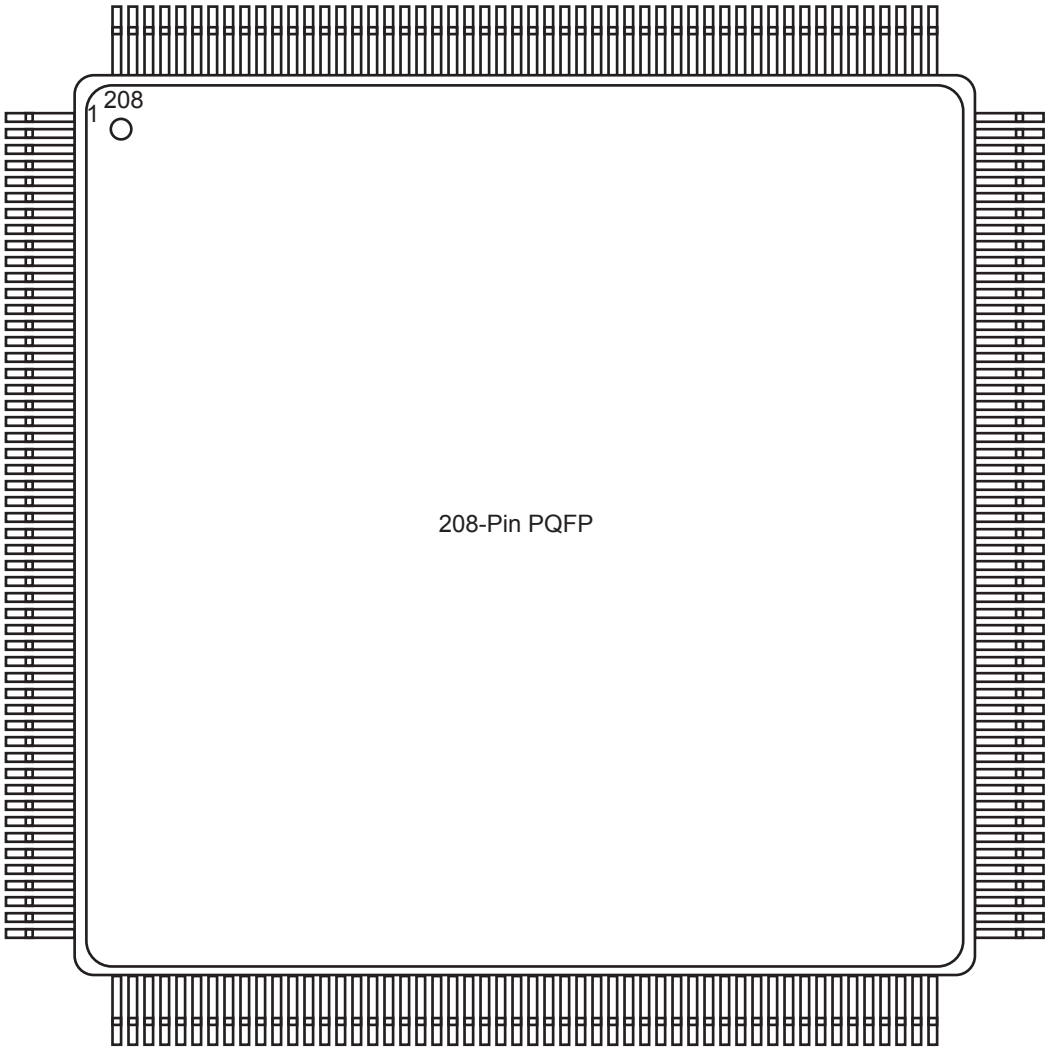
Table 2-101 • FIFO
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.38	1.57	1.84	ns
t_{ENH}	REN, WEN Hold Time	0.02	0.02	0.02	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (pass-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (pass-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET Removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET Recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency	310	272	231	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

4 – Package Pin Assignments

PQ208



Note: This is the top view of the package.

Note

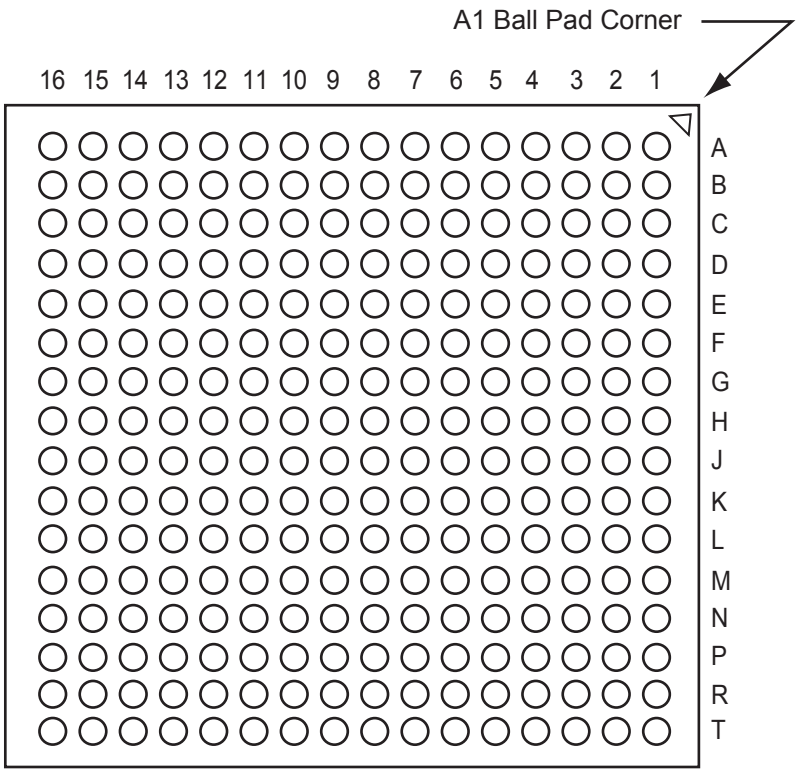
For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

PQ208	
Pin Number	A3PE3000 Function
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO308PSB7V4
5	GAA2/IO309PDB7V4
6	IO309NDB7V4
7	GAC2/IO307PDB7V4
8	IO307NDB7V4
9	IO303PDB7V3
10	IO303NDB7V3
11	IO299PDB7V3
12	IO299NDB7V3
13	IO295PDB7V2
14	IO295NDB7V2
15	IO291PSB7V2
16	VCC
17	GND
18	VCCIB7
19	IO285PDB7V1
20	IO285NDB7V1
21	IO279PSB7V0
22	GFC1/IO275PSB7V0
23	GFB1/IO274PDB7V0
24	GFB0/IO274NDB7V0
25	VCOMPLF
26	GFA0/IO273NPB6V4
27	VCCPLF
28	GFA1/IO273PPB6V4
29	GND
30	GFA2/IO272PDB6V4
31	IO272NDB6V4
32	GFB2/IO271PPB6V4
33	GFC2/IO270PPB6V4
34	IO271NPB6V4
35	IO270NPB6V4
36	VCC
37	IO252PDB6V2
38	IO252NDB6V2
39	IO248PSB6V1

PQ208	
Pin Number	A3PE3000 Function
40	VCCIB6
41	GND
42	IO244PDB6V1
43	IO244NDB6V1
44	GEC1/IO236PDB6V0
45	GEC0/IO236NDB6V0
46	GEB1/IO235PPB6V0
47	GEA1/IO234PPB6V0
48	GEB0/IO235NPB6V0
49	GEA0/IO234NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO233NDB5V4
56	GEA2/IO233PDB5V4
57	IO232NDB5V4
58	GEB2/IO232PDB5V4
59	IO231NDB5V4
60	GEC2/IO231PDB5V4
61	IO230PSB5V4
62	VCCIB5
63	IO218NDB5V3
64	IO218PDB5V3
65	GND
66	IO214PSB5V2
67	IO212NDB5V2
68	IO212PDB5V2
69	IO208NDB5V1
70	IO208PDB5V1
71	VCC
72	VCCIB5
73	IO202NDB5V1
74	IO202PDB5V1
75	IO198NDB5V0
76	IO198PDB5V0
77	IO197NDB5V0
78	IO197PDB5V0

PQ208	
Pin Number	A3PE3000 Function
79	IO194NDB5V0
80	IO194PDB5V0
81	GND
82	IO184NDB4V3
83	IO184PDB4V3
84	IO180NDB4V3
85	IO180PDB4V3
86	IO176NDB4V2
87	IO176PDB4V2
88	VCC
89	VCCIB4
90	IO170NDB4V2
91	IO170PDB4V2
92	IO166NDB4V1
93	IO166PDB4V1
94	IO156NDB4V0
95	GDC2/IO156PDB4V0
96	IO154NPB4V0
97	GND
98	GDB2/IO155PSB4V0
99	GDA2/IO154PPB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ
108	TDO
109	TRST
110	VJTAG
111	VMV3
112	GDA0/IO153NPB3V4
113	GDB0/IO152NPB3V4
114	GDA1/IO153PPB3V4
115	GDB1/IO152PPB3V4
116	GDC0/IO151NDB3V4
117	GDC1/IO151PDB3V4

FG256



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	A3PE3000 Function
H19	IO100PDB2V2
H20	VCC
H21	VMV2
H22	IO105PDB2V2
J1	IO285NDB7V1
J2	IO285PDB7V1
J3	VMV7
J4	IO279PDB7V0
J5	IO283PDB7V1
J6	IO281PDB7V0
J7	IO287NDB7V1
J8	VCCIB7
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB2
J16	IO84NDB2V0
J17	IO104NDB2V2
J18	IO104PDB2V2
J19	IO106PPB2V3
J20	GNDQ
J21	IO109PDB2V3
J22	IO107PDB2V3
K1	IO277NDB7V0
K2	IO277PDB7V0
K3	GNDQ
K4	IO279NDB7V0
K5	IO283NDB7V1
K6	IO281NDB7V0
K7	GFC1/IO275PPB7V0
K8	VCCIB7
K9	VCC
K10	GND

FG484	
Pin Number	A3PE3000 Function
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB2
K16	GCC1/IO112PPB2V3
K17	IO108NDB2V3
K18	IO108PDB2V3
K19	IO110NPB2V3
K20	IO106NPB2V3
K21	IO109NDB2V3
K22	IO107NDB2V3
L1	IO257PSB6V2
L2	IO276PDB7V0
L3	IO276NDB7V0
L4	GFB0/IO274NPB7V0
L5	GFA0/IO273NDB6V4
L6	GFB1/IO274PPB7V0
L7	VCOMPLF
L8	GFC0/IO275NPB7V0
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO112NPB2V3
L16	GCB1/IO113PPB2V3
L17	GCA0/IO114NPB3V0
L18	VCOMPLC
L19	GCB0/IO113NPB2V3
L20	IO110PPB2V3
L21	IO111NDB2V3
L22	IO111PDB2V3
M1	GNDQ
M2	IO255NPB6V2

FG484	
Pin Number	A3PE3000 Function
M3	IO272NDB6V4
M4	GFA2/IO272PDB6V4
M5	GFA1/IO273PDB6V4
M6	VCCPLF
M7	IO271NDB6V4
M8	GFB2/IO271PDB6V4
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO116PPB3V0
M16	GCA1/IO114PPB3V0
M17	GCC2/IO117PPB3V0
M18	VCCPLC
M19	GCA2/IO115PDB3V0
M20	IO115NDB3V0
M21	IO126PDB3V1
M22	IO124PSB3V1
N1	IO255PPB6V2
N2	IO253NDB6V2
N3	VMV6
N4	GFC2/IO270PPB6V4
N5	IO261PPB6V3
N6	IO263PDB6V3
N7	IO263NDB6V3
N8	VCCIB6
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB3
N16	IO116NPB3V0

FG676	
Pin Number	A3PE1500 Function
A1	GND
A2	GND
A3	GAA0/IO00NDB0V0
A4	GAA1/IO00PDB0V0
A5	IO06NDB0V0
A6	IO09NDB0V1
A7	IO09PDB0V1
A8	IO14NDB0V1
A9	IO14PDB0V1
A10	IO22NDB0V2
A11	IO22PDB0V2
A12	IO26NDB0V3
A13	IO26PDB0V3
A14	IO30NDB0V3
A15	IO30PDB0V3
A16	IO34NDB1V0
A17	IO34PDB1V0
A18	IO38NDB1V0
A19	IO38PDB1V0
A20	IO41PDB1V1
A21	IO44PDB1V1
A22	IO49PDB1V2
A23	IO50PDB1V2
A24	GBC1/IO55PDB1V3
A25	GND
A26	GND
AA1	IO174PDB6V0
AA2	IO171PDB6V0
AA3	GEA1/IO167PPB6V0
AA4	GEC0/IO169NPB6V0
AA5	VCOMPLE
AA6	GND
AA7	IO165NDB5V3
AA8	GEB2/IO165PDB5V3
AA9	IO163PDB5V3
AA10	IO159NDB5V3

FG676	
Pin Number	A3PE1500 Function
AA11	IO153NDB5V2
AA12	IO147NDB5V1
AA13	IO139NDB5V0
AA14	IO137NDB5V0
AA15	IO123NDB4V1
AA16	IO123PDB4V1
AA17	IO117NDB4V0
AA18	IO117PDB4V0
AA19	GDB2/IO112PDB4V0
AA20	GNDQ
AA21	TDO
AA22	GND
AA23	GND
AA24	IO102NDB3V1
AA25	IO102PDB3V1
AA26	IO98NDB3V1
AB1	IO174NDB6V0
AB2	IO171NDB6V0
AB3	GEB1/IO168PPB6V0
AB4	GEA0/IO167NPB6V0
AB5	VCCPLE
AB6	GND
AB7	GND
AB8	IO156NDB5V2
AB9	IO156PDB5V2
AB10	IO150PDB5V1
AB11	IO155PDB5V2
AB12	IO142PDB5V0
AB13	IO135NDB5V0
AB14	IO135PDB5V0
AB15	IO132PDB4V2
AB16	IO129PDB4V2
AB17	IO121PDB4V1
AB18	IO119NDB4V1
AB19	IO112NDB4V0
AB20	VMV4

FG676	
Pin Number	A3PE1500 Function
AB21	TCK
AB22	TRST
AB23	GDC0/IO108NDB3V2
AB24	GDC1/IO108PDB3V2
AB25	IO104NDB3V2
AB26	IO104PDB3V2
AC1	IO170PDB6V0
AC2	GEB0/IO168NPB6V0
AC3	IO166NPB5V3
AC4	GNDQ
AC5	GND
AC6	IO160PDB5V3
AC7	IO161PDB5V3
AC8	IO154PDB5V2
AC9	GND
AC10	IO150NDB5V1
AC11	IO155NDB5V2
AC12	IO142NDB5V0
AC13	IO138NDB5V0
AC14	IO138PDB5V0
AC15	IO132NDB4V2
AC16	IO129NDB4V2
AC17	IO121NDB4V1
AC18	IO119PDB4V1
AC19	IO118NDB4V0
AC20	IO118PDB4V0
AC21	IO114PPB4V0
AC22	TMS
AC23	VJTAG
AC24	VMV3
AC25	IO106NDB3V2
AC26	IO106PDB3V2
AD1	IO170NDB6V0
AD2	GEA2/IO166PPB5V3
AD3	VMV5
AD4	GEC2/IO164PDB5V3

Revision	Changes	Page
Revision 10 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34669).	I, 1-1
	The Y security option and Licensed DPA Logo were added to the "ProASIC3E Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34727).	III
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOOe devices via an IEEE 1532 JTAG interface" (SAR 34689).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34699).	1-6
	VCCPLL in Table 2-2 • Recommended Operating Conditions [1] was corrected from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 33851). The T_J symbol was added to the table and notes regarding T_A and T_J were removed. The second of two parameters in the VCCI and VMV row, called "3.3 V DC supply voltage," was corrected to "3.0 V DC supply voltage" (SAR 37227).	2-2
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P_{CLOCK}" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide* (SAR 34735).	2-9
	t_{DOUT} was corrected to t_{DIN} in Figure 2-3 • Input Buffer Timing Model and Delays (example) (SAR 37109).	2-13
	The typo related to the values for 3.3 V LVCMOS Wide Range in Table 2-17 • Summary of I/O Timing Characteristics—Software Default Settings was corrected (SAR 37227).	2-19
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section and "3.3 V LVCMOS Wide Range" section and tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34763).	2-18, 2-27

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-19 • I/O Output Buffer Maximum Resistances[1] and Table 2-21 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33853). 3.3 V LVCMOS Wide Range information was separated from regular 3.3 V LVCMOS and placed into its own new section, "3.3 V LVCMOS Wide Range". Values of IOSH and IOSL were added in Table 2-29 • Minimum and Maximum DC Input and Output Levels (SAR 33853).	2-20, 2-27
	The formulas in the table notes for Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34755).	2-21
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34889).	2-24
	The titles and subtitles for Table 2-31 • 3.3 V LVCMOS Wide Range High Slew and Table 2-32 • 3.3 V LVCMOS Wide Range Low Slew were corrected (SAR 37227).	2-28, 2-29
	The following notes were removed from Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 34812): ±5% Differential input voltage = ±350 mV	2-50
	Minimum pulse width High and Low values were added to the tables in the "Global Tree Timing Characteristics" section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36957).	2-68
	A note was added to Table 2-98 • ProASIC3E CCC/PLL Specification indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34824).	2-70
	The following figures were deleted. Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 34872). Figure 2-44 • Write Access after Write onto Same Address Figure 2-45 • Read Access after Write onto Same Address Figure 2-46 • Write Access after Read onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-49 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35750).	2-74, 2-75, 2-79, 2-82
	The "Pin Descriptions and Packaging" chapter is new (SAR 34771).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 34771).	4-1
	Pin E6 for the FG256 package was corrected from VvB0 to VCCIB0 (SARs 30364, 31597, 26243).	4-9
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3E Device Status" table on page II indicates the status for each device in the device family.	N/A